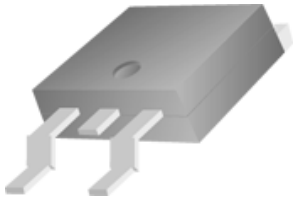
N-Channel 40-V (D-S) MOSFET

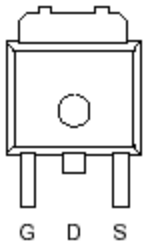
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
40	32 @ V_{GS} = 10V	33
	42 @ V_{GS} = 4.5V	29

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology



TO-252



Top View

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Units**
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[a]	T_C=25°C	I_D	33	A
Pulsed Drain Current[b]		I_{DM}	40	
Continuous Source Current (Diode Conduction)[a]		I_S	30	A
Power Dissipation[a]	T_C=25°C	P_D	50.0	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient[a]	$R_{\theta JA}$	50	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	°C/W

Notes

a. Surface Mounted on 1” x 1” FR4 Board.

b. Pulse width limited by maximum junction temperature

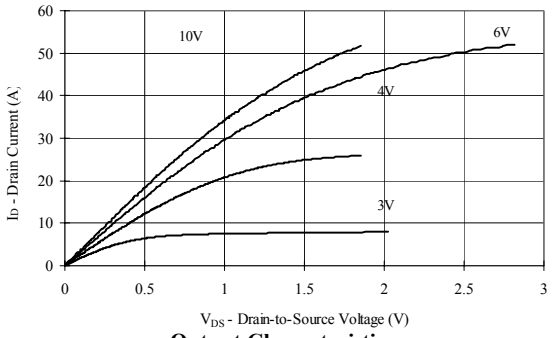
SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	1			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V			1	uA
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55°C			25	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	34			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 33 A			32	mΩ
		V_{GS} = 4.5 V, I_D = 29 A			42	
Forward Tranconductance[A]	g_{fs}	V_{DS} = 15 V, I_D = 33 A		22		S
Diode Forward Voltage	V_{SD}	I_S = 34 A, V_{GS} = 0 V		1.1		V
Pulsed Source Current (Body Diode)[A]	I_{SM}			5		A
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 33 A		5		nC
Gate-Source Charge	Q_{gs}			1.1		
Gate-Drain Charge	Q_{gd}			1.4		
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1MHz		489		pF
Output Capacitance	C_{oss}			94		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 25 V, R_L = 25 Ω , I_D = 34 A, V_{GEN} = 10 V		16		nS
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			23		
Fall-Time	t_f			3		

Notes

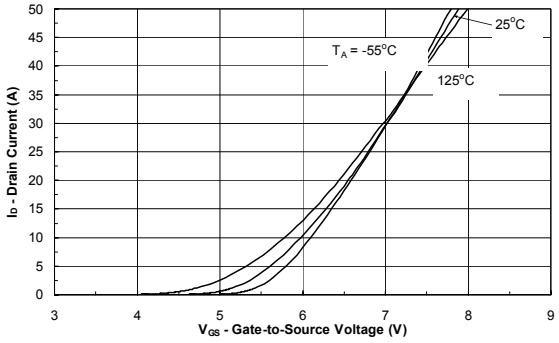
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

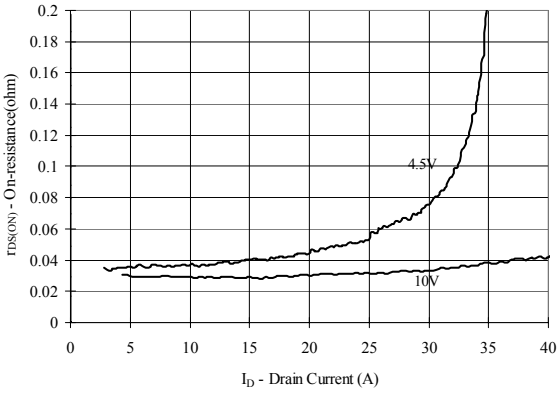
Typical Electrical Characteristics



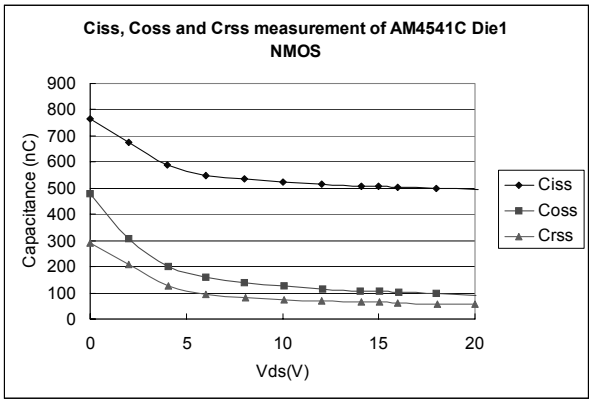
Output Characteristics



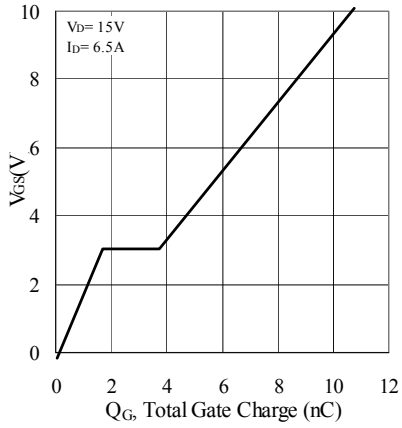
Transfer Characteristics



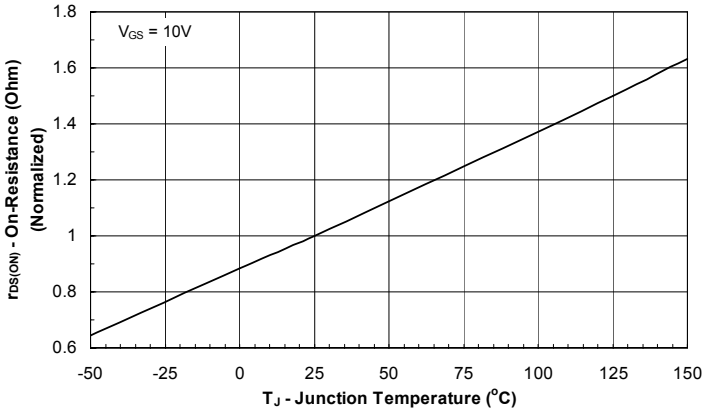
On Resistance vs. Drain Current



Capacitance

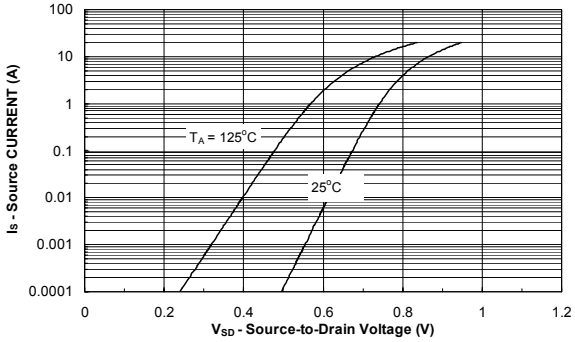


Gate Charge

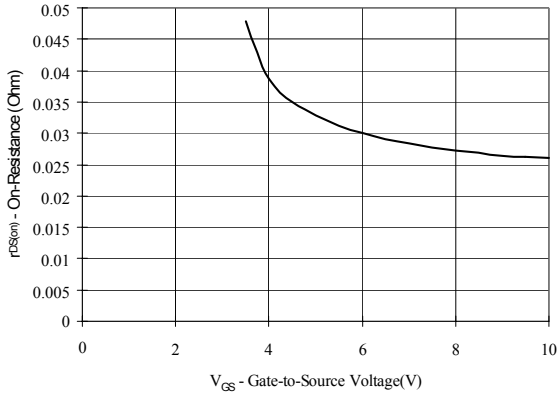


On-Resistance vs. Junction Temperature

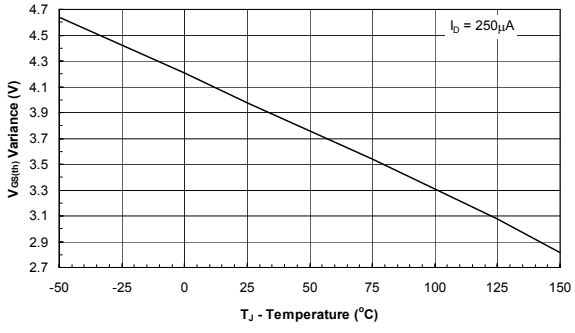
Typical Electrical Characteristics



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

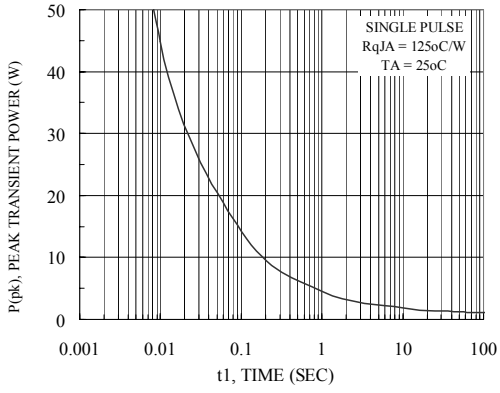


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

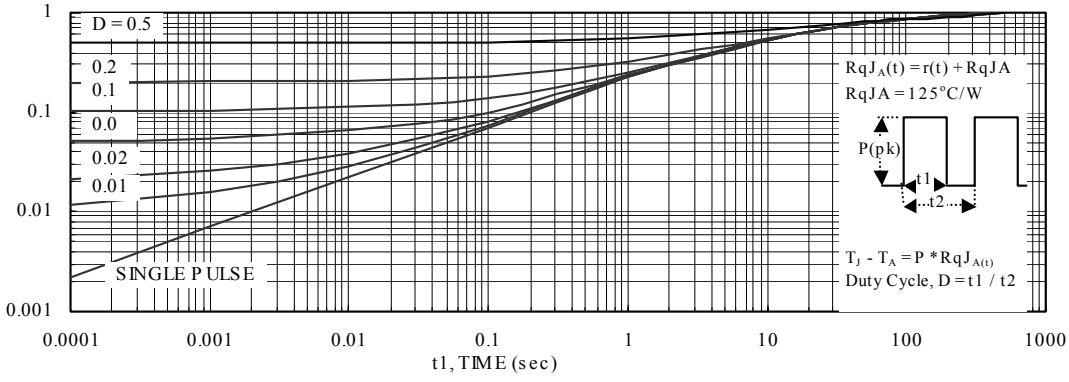
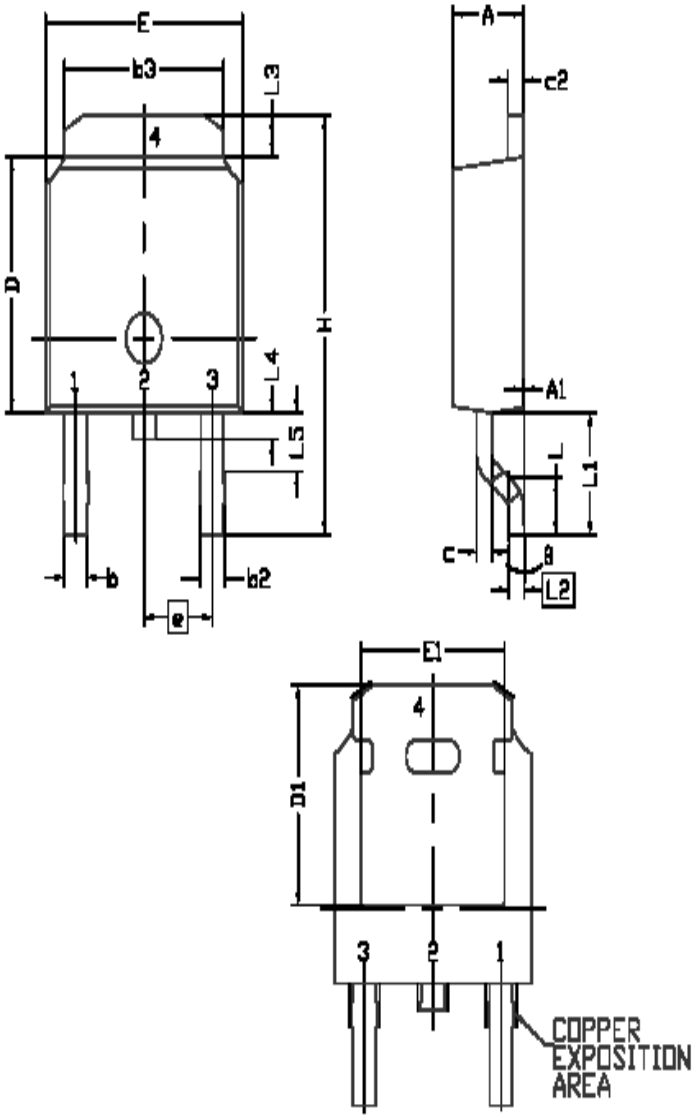


Figure 11. Transient Thermal Response Curve

Package Information



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	---	1.27
L4	0.64	---	1.01
L5	---	---	---
D	6.00	6.10	6.223
H	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0	---	0.127
c	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5.30	---	---
E1	4.40	---	---
θ	0°	---	10°